CLAIMS

1. A stripper solution for removing a resist from a substrate comprising the following ingredients:

60 wt % to 95 wt % of dimethyl sulfoxide,

water,

0.1 wt % to 5.0 wt % of hydroxylamine,

1.0 wt % of benzotriazole,

optionally 0.001 wt % to 1 wt % of one or more than one non-ionic surfactant,

optionally an additional corrosion inhibitor, and

1.75 wt % to 12.95 wt % of neat tetraethyl ammonium hydroxide,

wherein the stripper solution is free of fluorine-containing compounds and tetramethylammonium hydroxide, and

wherein the ingredients do not exceed 100 wt % of the solution.

2. The stripper solution of claim 1, wherein the stripper solution has a 5% pH of 11.39 to 12.69.

3. The stripper solution of claim 1, comprising 1.75 wt % of neat tetraethylammonium hydroxide.

4. The stripper solution of claim 1, comprising 3.5 wt % of neat tetraethylammonium hydroxide.

5. The stripper solution of claim 1, comprising 12.95 wt % of neat tetraethylammonium hydroxide.

6. The stripper solution of claim 1, comprising 1.75 wt % to 3.75 wt % of neat tetraethylammonium hydroxide.

7. The stripper solution of claim 1, comprising 3.75 wt % to 12.95 wt % of neat tetraethylammonium hydroxide.

8. The stripper solution of claim 1, comprising 1 wt % to 2.0 wt % of hydroxylamine.

9. The stripper solution of claim 1, comprising 1 wt % to 2.0 wt % of hydroxylamine and 3.5 wt % to 12.95 wt % of neat tetraethylammonium hydroxide.

10. The stripper solution of claim 9, comprising 60 wt % of dimethyl sulfoxide.

11. The stripper solution of claim 1, comprising the optional additional corrosion inhibitor, wherein the additional corrosion inhibitor is selected from the group consisting of carboxybenzotriazole, amino-benzotriazole, D-fructose, t-butyl catechol, L-ascorbic acid, vanillin, salicylic acid, diethyl hydroxylamine, poly(ethyleneimine), o-tolyltriazole, m tolyltriazole, and p-tolyltriazole and 2-mercaptobenzimidazole.

12. The stripper solution of claim 9, comprising 87 wt % of dimethyl sulfoxide.

13. The stripper solution of claim 1, comprising from 1 to 12.95 wt % of neat tetraethylammonium hydroxide and from 1 to 15 wt % water.

14. The stripper solution of claim 1, comprising the optional non-ionic surfactant, wherein the non-ionic surfactant selected from the group consisting of bis(2-ethylhexyl)phosphate, perfluoroheptanoic acid, prefluorodecanoic acid, trifluoromethanesulfonic acid, phosphonoacetic acid, dodecenylsuccinic acid, dioctadecyl hydrogen phosphate, octadecyl dihydrogen phosphate, dodecylamine, dodecenylsuccinic acid monodiethanol amide, lauric acid, palmitic acid, oleic acid, juniperic acid, 12 hydroxystearic acid, dodecyl phosphate and acetylene glycol surfactant.

15. The stripper solution of claim 1, wherein water comprises from 3.5 wt % to 9 wt % of the composition; and the hydroxylamine comprises more than or equal to 1 wt % but less than or equal to 2 wt % of the composition.

16. A method for removing a resist from a substrate comprising: (a) providing a substrate having a resist thereon; (b) contacting the substrate with a stripper solution for a time sufficient to remove the resist; (c) removing the substrate from the stripper solution; and (d) rinsing the stripper solution from the substrate with a solvent, wherein the step of contacting the substrate with a stripper solution involves contacting the substrate with a stripper solution of any of the preceding claims.

17. The method of claim 16, wherein contacting the substrate with a stripper solution includes immersing the substrate in the stripper solution with agitation at a temperature of at least 40 ºC.

18. The method of claim 16, wherein contacting the substrate with a stripper solution includes immersing the substrate in the stripper solution with agitation at a temperature of less than 40 ºC.

19. The method of claim 16, wherein contacting the substrate with a stripper solution includes spraying the stripper solution onto the substrate, wherein the stripper solution is at a temperature of at least 40 ºC.

20. The method of claim 16, wherein contacting the substrate with a stripper solution includes spraying the stripper solution onto the substrate, wherein the stripper solution is at a temperature of less than 40 ºC.

21. The method of claim 16, wherein providing a substrate having a resist thereon, involves providing a substrate having a resist which is a bilayer resist having two polymer layers.

22. The method of claim 16, wherein providing a substrate having a resist thereon, involves providing a substrate having a resist which is a bilayer resist having one inorganic layer and one polymer layer.

23. A method for preparing a stripper solution, the method comprising: (a) providing a container; (b) providing components of the stripper solution; and (c) adding said components of said stripper solution to said container to provide contents, wherein said providing components involves providing the following ingredients:

60 wt % to 95 wt % of dimethyl sulfoxide,
water,
0.1 wt % to 5.0 wt % of hydroxylamine,
1.0 wt % of benzotriazole,
optionally 0.001 wt % to 1 wt % of one or more than one non-ionic surfactant,
optionally an additional corrosion inhibitor, and
1.75 wt % to 12.95 wt % of neat tetraethyl ammonium hydroxide,

wherein the stripper solution is free of fluorine-containing compounds and tetramethylammonium hydroxide, and

wherein the ingredients do not exceed 100 wt % of the solution.

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